

31 ~~33~~<sup>34</sup> (Previously Presented) The system of claim ~~36~~<sup>34</sup>, wherein electric charges drawn across the semiconductor layer is greater near the first surface of the semiconductor layer adjacent to the charge-collection layer relative to the second surface.

32 ~~34~~<sup>34</sup> (Previously Presented) The digital radiography system of claim ~~36~~<sup>34</sup>, wherein the flat panel imager is a TFT-based imager.

33 ~~35~~<sup>34</sup> (Previously Presented) The digital radiography system of claim ~~36~~<sup>34</sup>, wherein the flat panel imager is a CCD-based imager.

34 ~~36~~ (Previously Presented) A digital radiography system, comprising:  
an x-ray source to transmit x-rays;  
a flat panel imager to receive the x-rays and to produce a digitized image,  
comprising:  
a semiconductor layer disposed above a charge-collection layer;  
a bias electrode layer disposed above the semiconductor layer, the  
bias electrode to generate an electric field within the semiconductor layer;  
and  
a casing that holds the flat panel imager together, wherein the  
casing forms an aperture window to receive the x-rays; and  
a display system connected to the flat panel imager, the display system to  
display the digitized image, wherein the semiconductor layer has a first surface  
adjacent to the charge-collection layer and a second surface adjacent to the bias  
electrode, and wherein the flat panel imager is configured such that x-rays traverse  
the charge-collection layer before propagating through the semiconductor layer.